10-PZ06NIA030SA-P924F33Y

datasheet

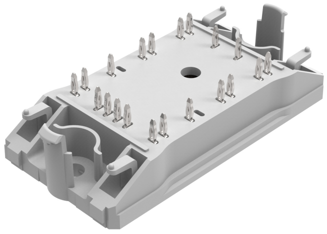
Vincotech

***flow*NPC 0 IGBT** **600 V / 30 A**

Topology features

- Kelvin Emitter for improved switching performance
- Neutral Point Clamped Topology (I-Type)
- Temperature sensor

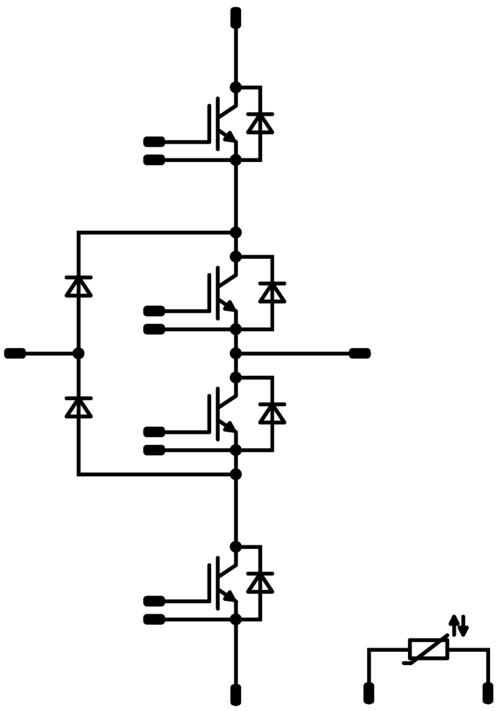
flow 0 12 mm housing



Component features

- Easy paralleling
- Low turn-off losses
- Low collector emitter saturation voltage
- Positive temperature coefficient
- Short tail current

Schematic



Housing features

- Base isolation: Al_2O_3
- Clip-in, reliable mechanical connection, qualified for wave soldering
- Convex shaped substrate for superior thermal contact
- Thermo-mechanical push-and-pull force relief
- Press-fit pin
- Reliable cold welding connection

Target applications

- UPS
- Solar Inverters

Types

- 10-PZ06NIA030SA-P924F33Y

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Value	Unit
Buck Switch					
Collector-emitter voltage	V_{CES}			600	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$	T_s = 80 °C	33	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}		90	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	64	W
Gate-emitter voltage	V_{GES}			±20	V
Short circuit ratings	t_{SC}	V_{GE} = 15 V, V_{CC} = 360 V	T_j = 150 °C	6	μs
Maximum junction temperature	T_{jmax}			175	°C
Buck Diode					
Peak repetitive reverse voltage	V_{RRM}			600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	33	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		60	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	52	W
Maximum junction temperature	T_{jmax}			175	°C
Boost Switch					
Collector-emitter voltage	V_{CES}			600	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$	T_s = 80 °C	33	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}		90	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	64	W
Gate-emitter voltage	V_{GES}			±20	V
Short circuit ratings	t_{SC}	V_{GE} = 15 V, V_{CC} = 360 V	T_j = 150 °C	6	μs
Maximum junction temperature	T_{jmax}			175	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Value	Unit
Boost Diode					
Peak repetitive reverse voltage	V_{RRM}			600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	33	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		60	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	52	W
Maximum junction temperature	T_{jmax}			175	°C
Boost Sw. Inv. Diode					
Peak repetitive reverse voltage	V_{RRM}			600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	33	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		60	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	52	W
Maximum junction temperature	T_{jmax}			175	°C
Module Properties					
Thermal Properties					
Storage temperature	T_{stg}			-40…+125	°C
Operation temperature under switching condition	T_{jop}			-40…+(T_{jmax} - 25)	°C
Isolation Properties					
Isolation voltage	V_{isol}	DC Test Voltage*	t_p = 2 s	6000	V
Isolation voltage	V_{isol}	AC Voltage	t_p = 1 min	2500	V
Creepage distance				min. 12,7	mm
Clearance				9	mm
Comparative Tracking Index	CTI			≥ 200	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Buck Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,00043	25	5	5,8	6,5	V
Collector-emitter saturation voltage	V_{CEsat}		15		30	25 150	1,1	1,57 1,8	1,9(1)	V
Collector-emitter cut-off current	I_{CES}		0	600		25			1,6	µA
Gate-emitter leakage current	I_{GES}		20	0		25			300	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}	f = 1 Mhz	0	25		25		1630		pF
Output capacitance	C_{oes}							108		pF
Reverse transfer capacitance	C_{res}							50		pF
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,49		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 16 Ω R_{goff} = 16 Ω	±15	350	30	25 125		98,4 101,4		ns
Rise time	t_r					25 125		11,4 16,4		ns
Turn-off delay time	$t_{d(off)}$					25 125		155,4 173,6		ns
Fall time	t_f					25 125		93,1 107,02		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=1,41 µC Q_{rFWD}=2,29 µC				25 125		0,474 0,618		mWs
Turn-off energy (per pulse)	E_{off}					25 125		0,802 1,01		mWs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Buck Diode										
Static										
Forward voltage	V_F				30	25 150	1,25	1,64 1,55	1,95(1)	V
Reverse leakage current	I_R	V_r = 600 V				25			27	µA
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,81		K/W
Dynamic										
Peak recovery current	I_{RRM}	d*i*/d*t*=3840 A/µs d*i*/d*t*=2458 A/µs	±15	350	30	25 125		35,98 39,02		A
Reverse recovery time	t_{rr}					25 125		126,45 183,17		ns
Recovered charge	Q_r					25 125		1,41 2,29		µC
Reverse recovered energy	E_{rec}					25 125		0,327 0,554		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125		4073 2293		A/µs

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Values Min	Typ	Max	Unit
Boost Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,00043	25	5	5,8	6,5	V
Collector-emitter saturation voltage	V_{CEsat}		15		30	25 150	1,1	1,57 1,8	1,9(1)	V
Collector-emitter cut-off current	I_{CES}		0	600		25			1,6	µA
Gate-emitter leakage current	I_{GES}		20	0		25			300	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}	f = 1 Mhz	0	25		25		1630		pF
Output capacitance	C_{oes}	f = 1 Mhz	0	25		25		108		pF
Reverse transfer capacitance	C_{res}	f = 1 Mhz	0	25		25		50		pF
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,49		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 16 Ω R_{goff} = 16 Ω	±15	350	30	25 125		101,6 102,4		ns
Rise time	t_r	R_{gon} = 16 Ω R_{goff} = 16 Ω	±15	350	30	25 125		15,4 17,8		ns
Turn-off delay time	$t_{d(off)}$	R_{gon} = 16 Ω R_{goff} = 16 Ω	±15	350	30	25 125		158,2 177,2		ns
Fall time	t_f	R_{gon} = 16 Ω R_{goff} = 16 Ω	±15	350	30	25 125		87,95 105,11		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=1,36 µC Q_{rFWD}=2,52 µC	±15	350	30	25 125		0,452 0,594		mWs
Turn-off energy (per pulse)	E_{off}		±15	350	30	25 125		0,809 1,04		mWs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Boost Diode										
Static										
Forward voltage	V_F				30	25 150	1,25	1,64 1,55	1,95(1)	V
Reverse leakage current	I_R	V_r = 600 V				25			27	µA
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,81		K/W
Dynamic										
Peak recovery current	I_{RRM}	di/dt=2467 A/µs di/dt=1930 A/µs	±15	350	30	25 125		27,63 30,48		A
Reverse recovery time	t_{rr}					25 125		138,03 264,77		ns
Recovered charge	Q_r					25 125		1,36 2,52		µC
Reverse recovered energy	E_{rec}					25 125		0,336 0,667		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125		1297 449,65		A/µs
Boost Sw. Inv. Diode										
Static										
Forward voltage	V_F				30	25 150	1,25	1,64 1,55	1,95(1)	V
Reverse leakage current	I_R	V_r = 600 V				25			27	µA
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,81		K/W

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Thermistor										
Static										
Rated resistance	R					25		22		kΩ
Deviation of R_{100}	$\Delta_{R/R}$	R_{100} = 1486 Ω				100	-12		14	%
Power dissipation	P							200		mW
Power dissipation constant	d					25		2		mW/K
B-value	$B_{(25/50)}$	Tol. ±3 %						3950		K
B-value	$B_{(25/100)}$	Tol. ±3 %						3998		K
Vincotech Thermistor Reference									B	

(1) Value at chip level

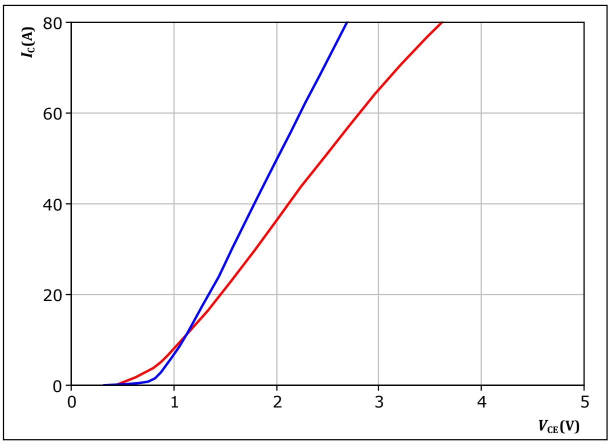
(2) Only valid with pre-applied Vincotech thermal interface material.

Buck Switch Characteristics

figure 1. IGBT

Typical output characteristics

I_C = f(V_{CE})



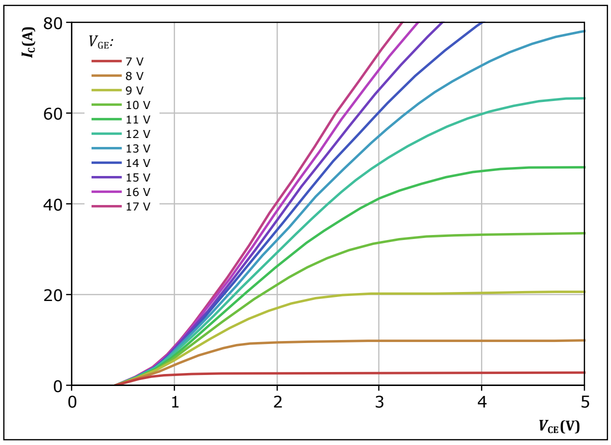
t_p =	250	µs
V_{GE} =	15	V

T_j: 25 °C, 150 °C

figure 2. IGBT

Typical output characteristics

I_C = f(V_{CE})



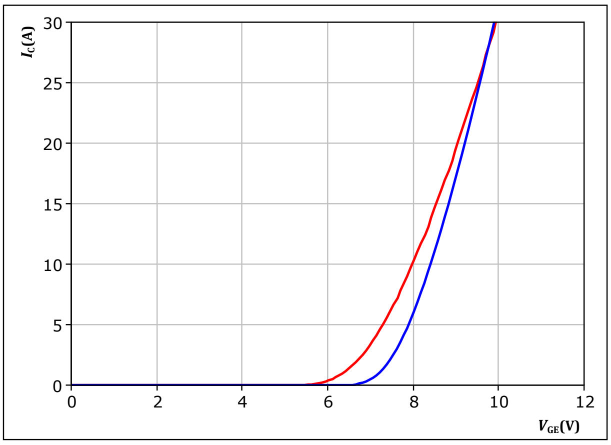
t_p =	250	µs
T_j =	150	°C

V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. IGBT

Typical transfer characteristics

I_C = f(V_{GE})



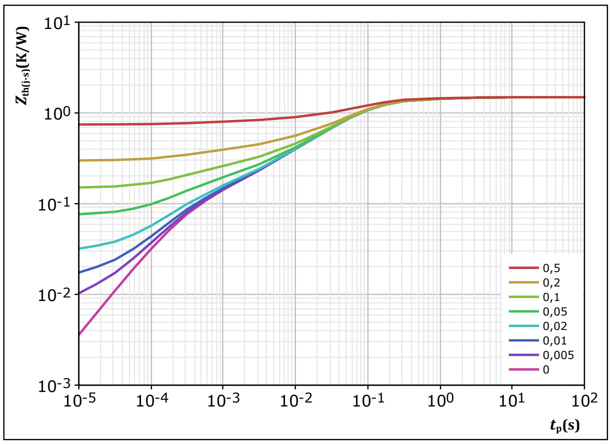
t_p =	250	µs
V_{CE} =	10	V

T_j: 25 °C, 150 °C

figure 4. IGBT

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D =	t_p / T	
$R_{th(j-s)}$ =	1,49	K/W

IGBT thermal model values

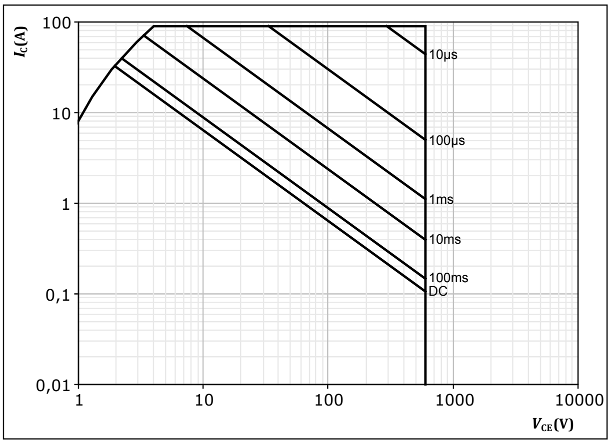
R (K/W)	τ (s)
7,25E-02	2,15E+00
1,02E-01	4,82E-01
6,96E-01	9,49E-02
3,56E-01	3,40E-02
1,42E-01	5,95E-03
4,77E-02	1,04E-03
7,51E-02	2,72E-04

Buck Switch Characteristics

figure 5. **IGBT**

Safe operating area

$I_C = f(V_{CE})$



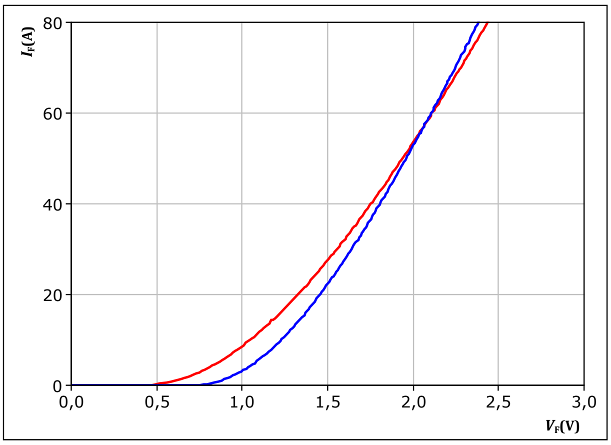
D =	single pulse	
T_s =	80	°C
V_{GE} =	15	V
T_j =	T_{jmax}	

Buck Diode Characteristics

figure 6. **FWD**

Typical forward characteristics

$I_F = f(V_F)$



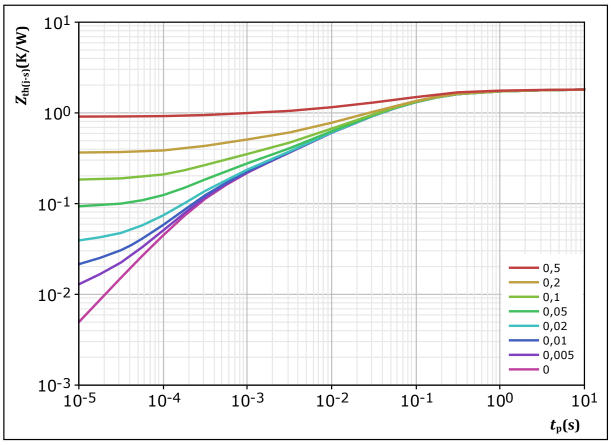
t_p = 250 µs

T_j: 25 °C, 150 °C

figure 7. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



$D = t_p / T$

$R_{th(j-s)}$ = 1,811 K/W

FWD thermal model values

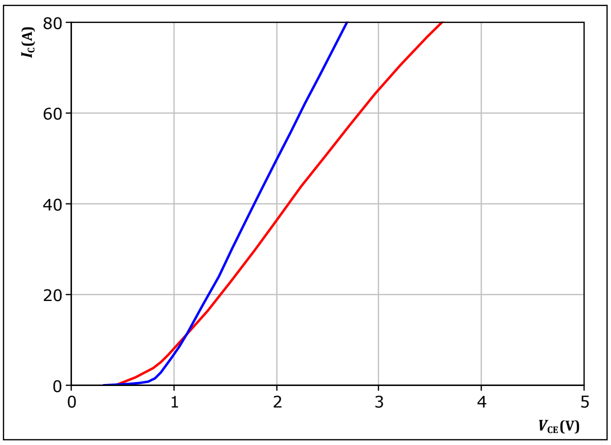
R (K/W)	τ (s)
8,35E-02	4,59E+00
2,01E-01	4,81E-01
7,60E-01	9,25E-02
4,22E-01	1,80E-02
2,13E-01	3,31E-03
1,40E-01	3,46E-04

Boost Switch Characteristics

figure 8. **IGBT**

Typical output characteristics

I_C = f(V_{CE})



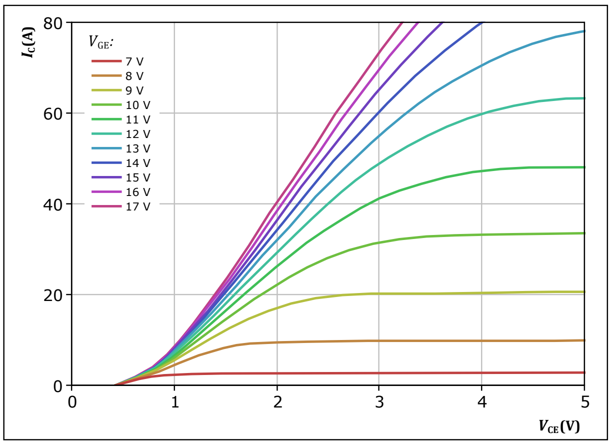
t_p =	250	µs
V_{GE} =	15	V

T_j: 25 °C, 150 °C

figure 9. **IGBT**

Typical output characteristics

I_C = f(V_{CE})



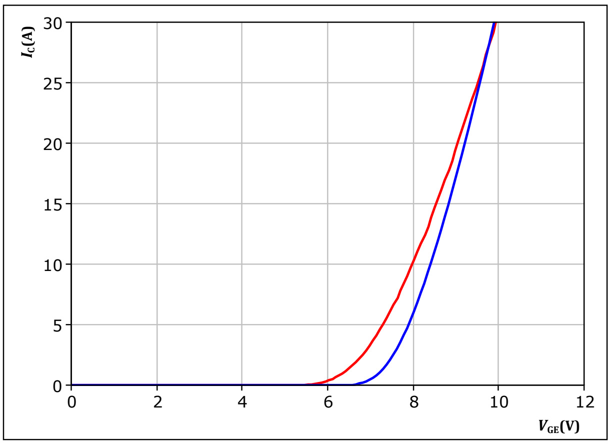
t_p =	250	µs
T_j =	150	°C

V_{GE} from 7 V to 17 V in steps of 1 V

figure 10. **IGBT**

Typical transfer characteristics

I_C = f(V_{GE})



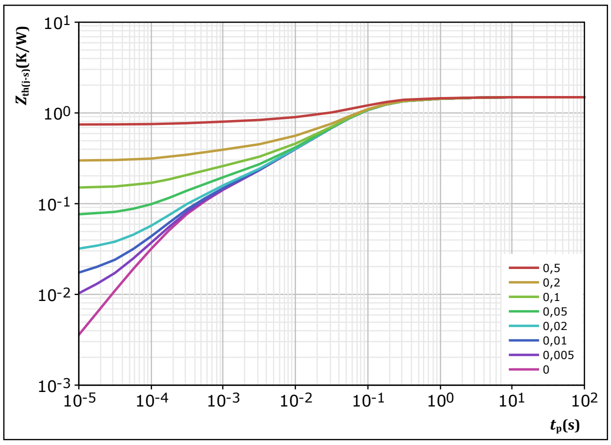
t_p =	250	µs
V_{CE} =	10	V

T_j: 25 °C, 150 °C

figure 11. **IGBT**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 1,49 K/W

IGBT thermal model values

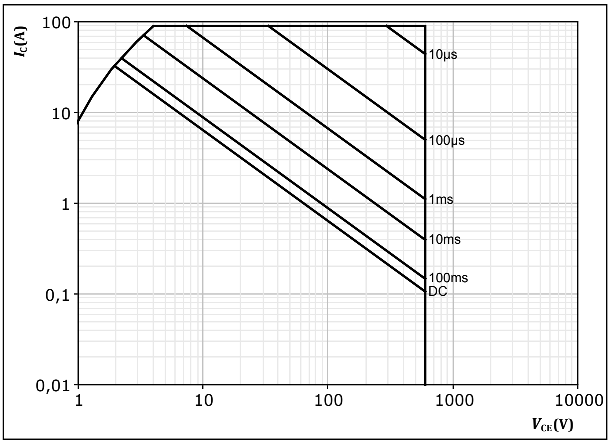
R (K/W)	τ (s)
7,25E-02	2,15E+00
1,02E-01	4,82E-01
6,96E-01	9,49E-02
3,56E-01	3,40E-02
1,42E-01	5,95E-03
4,77E-02	1,04E-03
7,51E-02	2,72E-04

Boost Switch Characteristics

figure 12.	IGBT

Safe operating area

$I_C = f(V_{CE})$



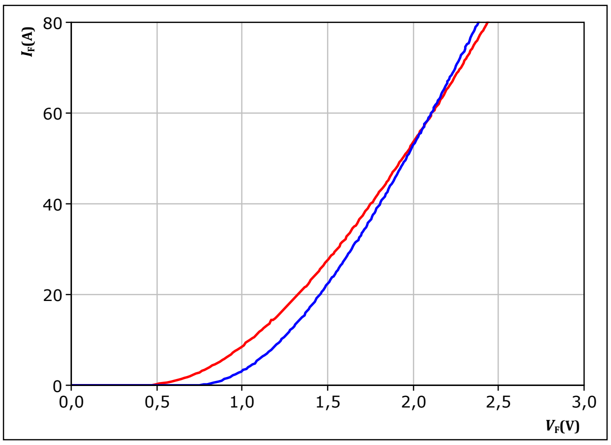
D =	single pulse	
T_s =	80	°C
V_{GE} =	15	V
T_j =	T_{jmax}	

Boost Diode Characteristics

figure 13. FWD

Typical forward characteristics

I_F = f(V_F)



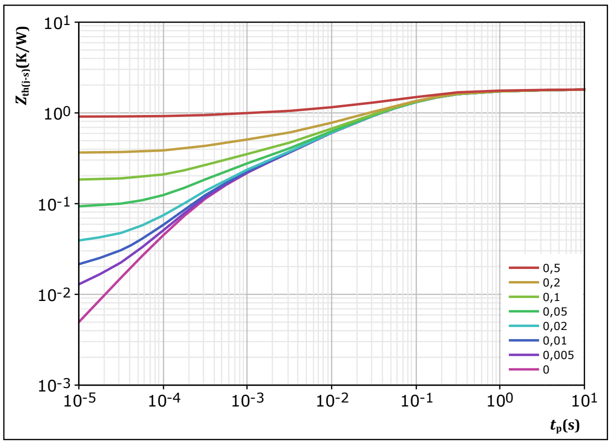
t_p = 250 µs

T_j: 25 °C, 150 °C

figure 14. FWD

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 1,811 K/W

FWD thermal model values

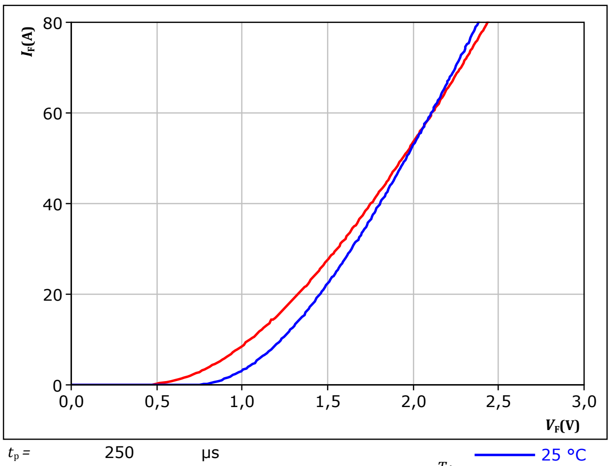
R (K/W)	τ (s)
8,35E-02	4,59E+00
2,01E-01	4,81E-01
7,60E-01	9,25E-02
4,22E-01	1,80E-02
2,13E-01	3,31E-03
1,40E-01	3,46E-04

Boost Sw. Inv. Diode Characteristics

figure 15. FWD

Typical forward characteristics

I_F = f(V_F)



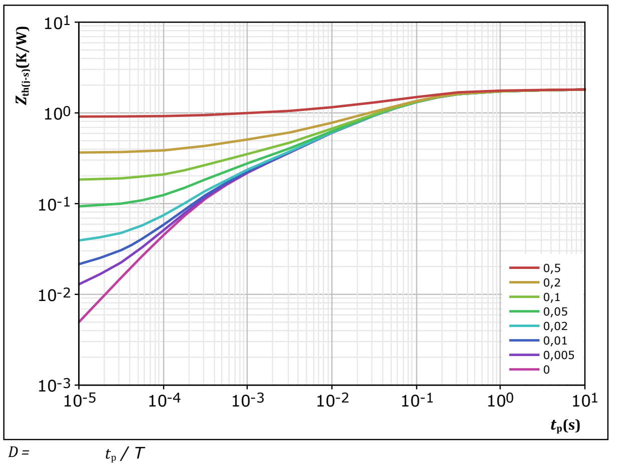
t_p = 250 µs

T_j: 25 °C, 150 °C

figure 16. FWD

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 1,811 K/W

FWD thermal model values

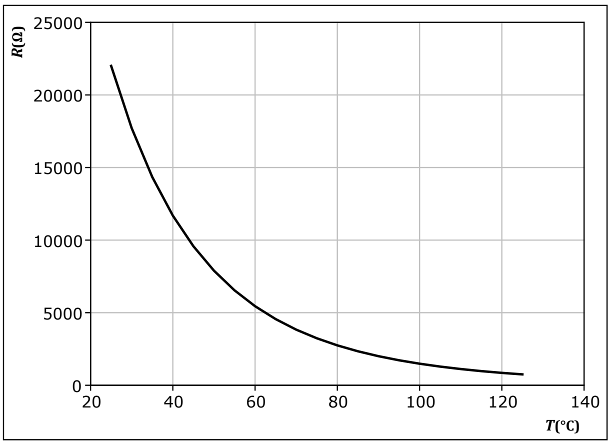
R (K/W)	τ (s)
8,35E-02	4,59E+00
2,01E-01	4,81E-01
7,60E-01	9,25E-02
4,22E-01	1,80E-02
2,13E-01	3,31E-03
1,40E-01	3,46E-04

Thermistor Characteristics

figure 17. **Thermistor**

Typical NTC characteristic as function of temperature

R_T = f(T)

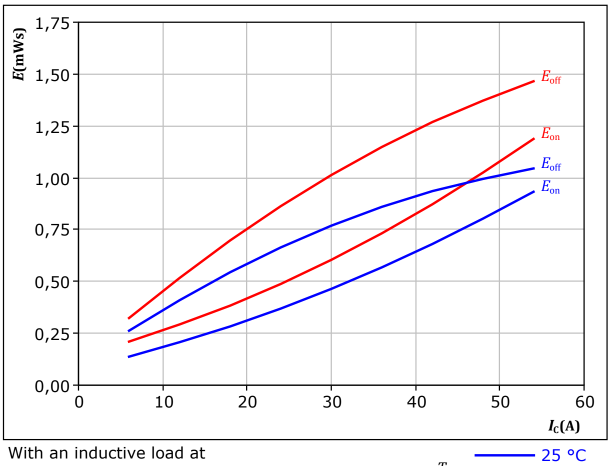


Buck Switching Characteristics

figure 18. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



With an inductive load at

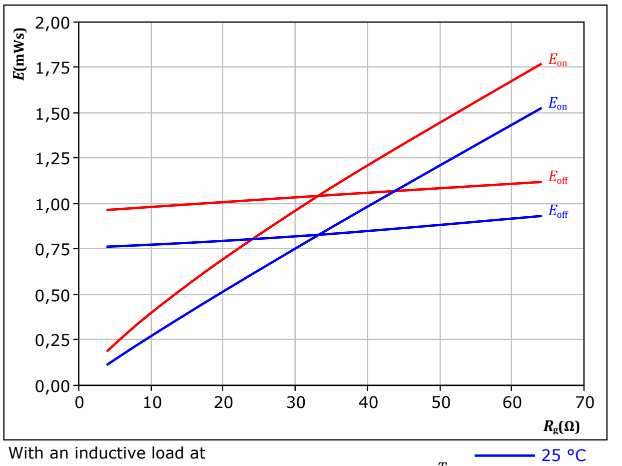
T_j: 25 °C / 125 °C

V_{CE} =	350	V
V_{GE} =	±15	V
R_{gon} =	16	Ω
R_{goff} =	16	Ω

figure 19. **IGBT**

Typical switching energy losses as a function of IGBT turn on gate resistor

$E = f(R_g)$



With an inductive load at

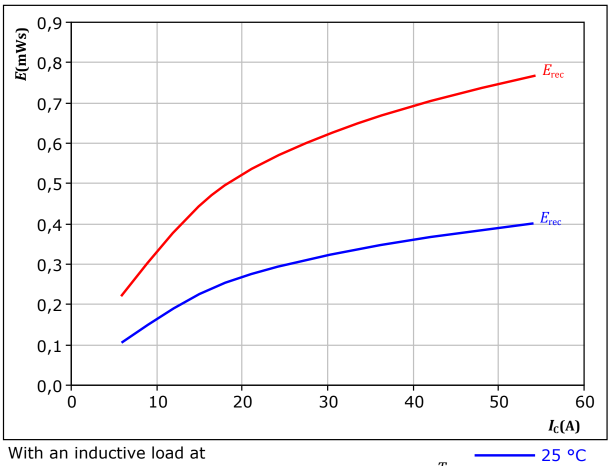
T_j: 25 °C / 125 °C

V_{CE} =	350	V
V_{GE} =	±15	V
I_C =	30	A

figure 20. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_C)$



With an inductive load at

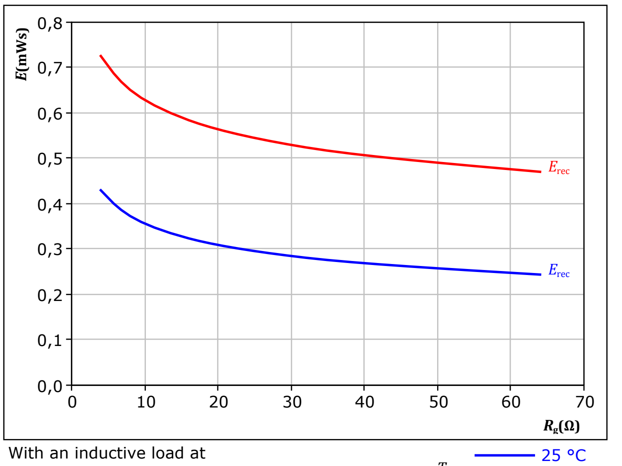
T_j: 25 °C / 125 °C

V_{CE} =	350	V
V_{GE} =	±15	V
R_{gon} =	16	Ω

figure 21. **FWD**

Typical reverse recovered energy loss as a function of IGBT turn on gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

T_j: 25 °C / 125 °C

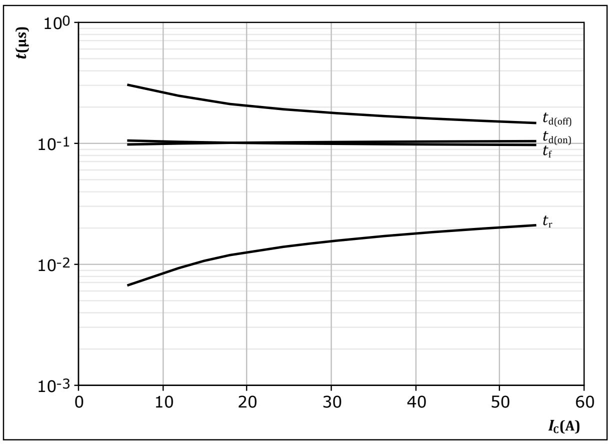
V_{CE} =	350	V
V_{GE} =	±15	V
I_C =	30	A

Buck Switching Characteristics

figure 22. **IGBT**

Typical switching times as a function of collector current

t = f(I_C)



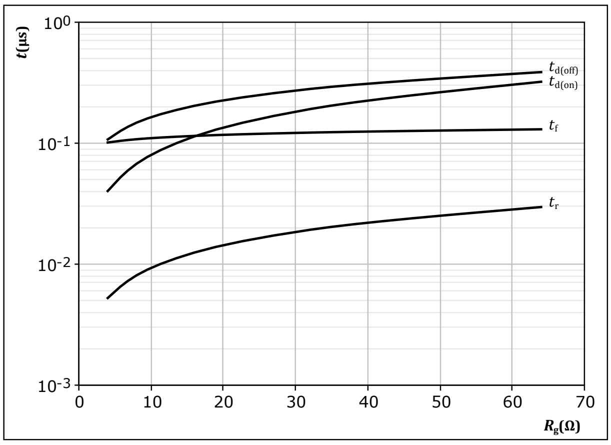
With an inductive load at

T_j =	125	°C
V_{CE} =	350	V
V_{GE} =	±15	V
R_{gon} =	16	Ω
R_{goff} =	16	Ω

figure 23. **IGBT**

Typical switching times as a function of IGBT turn on gate resistor

t = f(R_g)



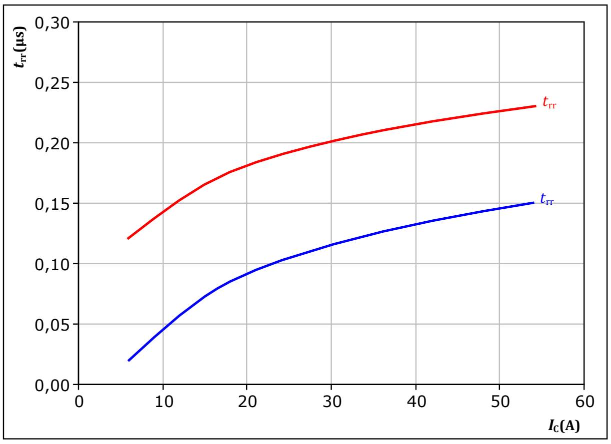
With an inductive load at

T_j =	125	°C
V_{CE} =	350	V
V_{GE} =	±15	V
I_C =	30	A

figure 24. **FWD**

Typical reverse recovery time as a function of collector current

t_{rr} = f(I_C)



With an inductive load at

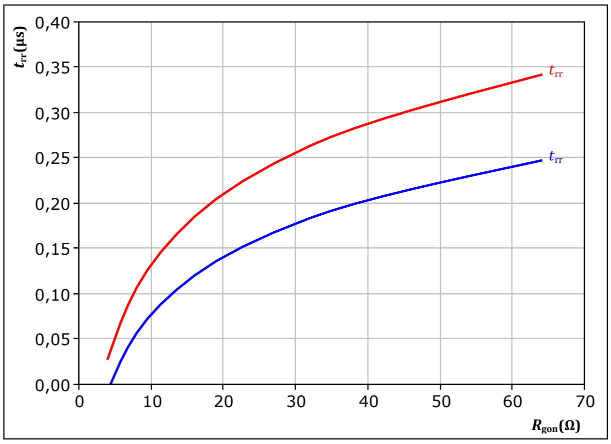
V_{CE} =	350	V
V_{GE} =	±15	V
R_{gon} =	16	Ω

T_j: 25 °C, 125 °C

figure 25. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

t_{rr} = f(R_{gon})



With an inductive load at

V_{CE} =	350	V
V_{GE} =	±15	V
I_C =	30	A

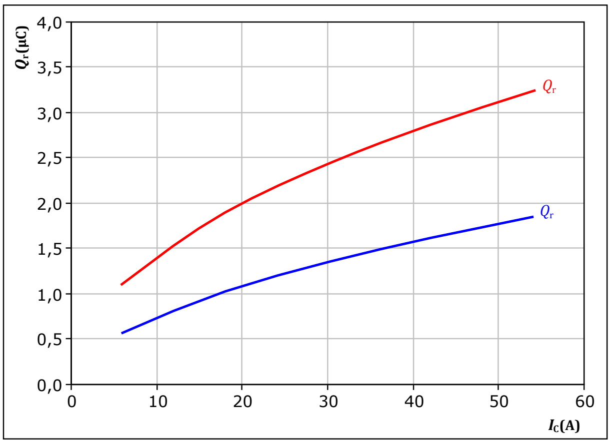
T_j: 25 °C, 125 °C

Buck Switching Characteristics

figure 26. **FWD**

Typical recovered charge as a function of collector current

Q_r = f(I_C)



With an inductive load at

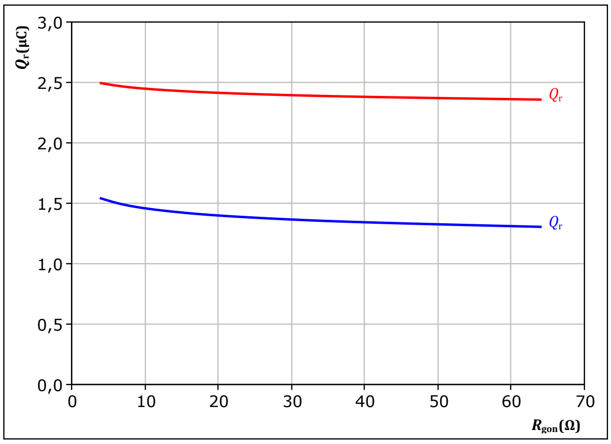
T_j: 25 °C / 125 °C

V_{CE} =	350	V
V_{GE} =	±15	V
R_{gon} =	16	Ω

figure 27. **FWD**

Typical recovered charge as a function of IGBT turn on gate resistor

Q_r = f(R_{gon})



With an inductive load at

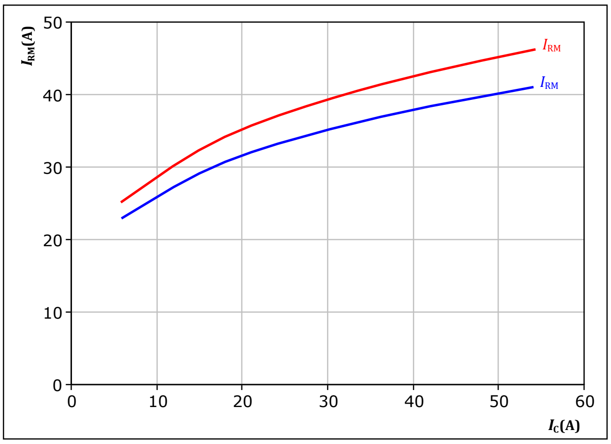
T_j: 25 °C / 125 °C

V_{CE} =	350	V
V_{GE} =	±15	V
I_C =	30	A

figure 28. **FWD**

Typical peak reverse recovery current as a function of collector current

I_{RM} = f(I_C)



With an inductive load at

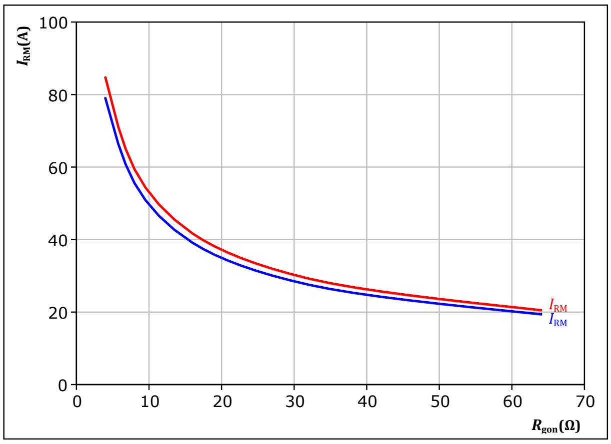
T_j: 25 °C / 125 °C

V_{CE} =	350	V
V_{GE} =	±15	V
R_{gon} =	16	Ω

figure 29. **FWD**

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

I_{RM} = f(R_{gon})



With an inductive load at

T_j: 25 °C / 125 °C

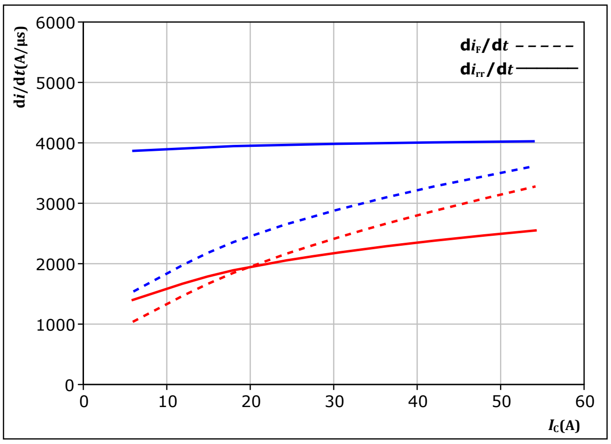
V_{CE} =	350	V
V_{GE} =	±15	V
I_C =	30	A

Buck Switching Characteristics

figure 30. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, di_{rr}/dt = f(I_C)



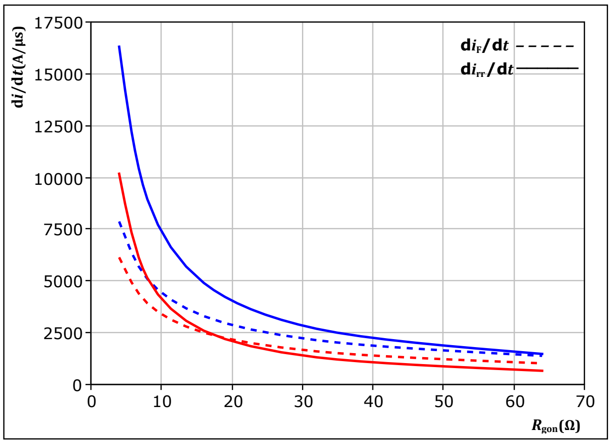
With an inductive load at

V_{CE} =	350	V	T_j: 25 °C / 125 °C
V_{GE} =	±15	V	
R_{gon} =	16	Ω	

figure 31. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})



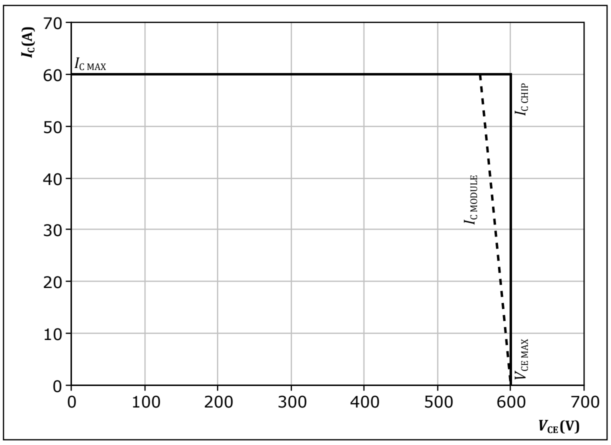
With an inductive load at

V_{CE} =	350	V	T_j: 25 °C / 125 °C
V_{GE} =	±15	V	
I_C =	30	A	

figure 32. **IGBT**

Reverse bias safe operating area

I_C = f(V_{CE})



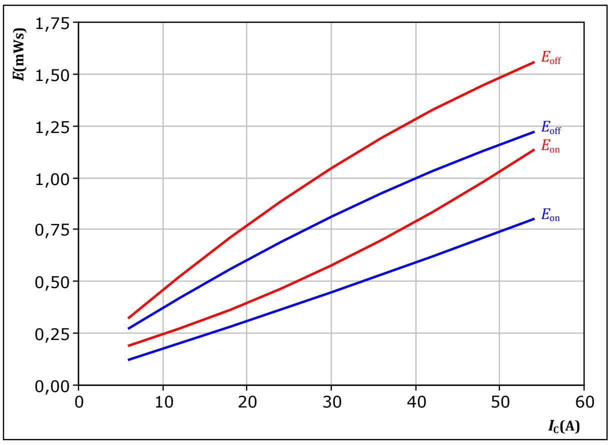
At	T_j =	125	°C
	R_{gon} =	16	Ω
	R_{goff} =	16	Ω

Boost Switching Characteristics

figure 33. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



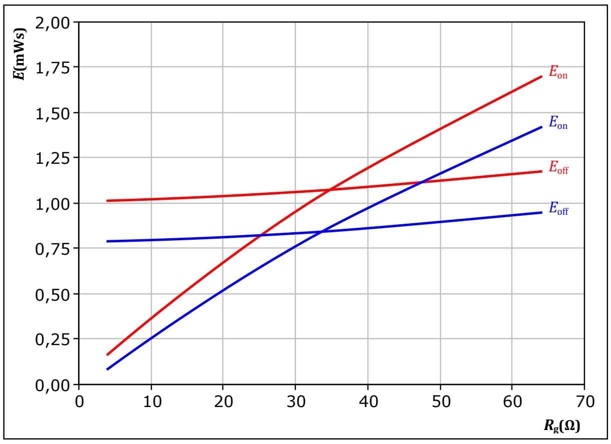
With an inductive load at

V_{CE} =	350	V	T_j: 25 °C / 125 °C
V_{GE} =	±15	V	
R_{gon} =	16	Ω	
R_{goff} =	16	Ω	

figure 34. **IGBT**

Typical switching energy losses as a function of IGBT turn on gate resistor

$E = f(R_g)$



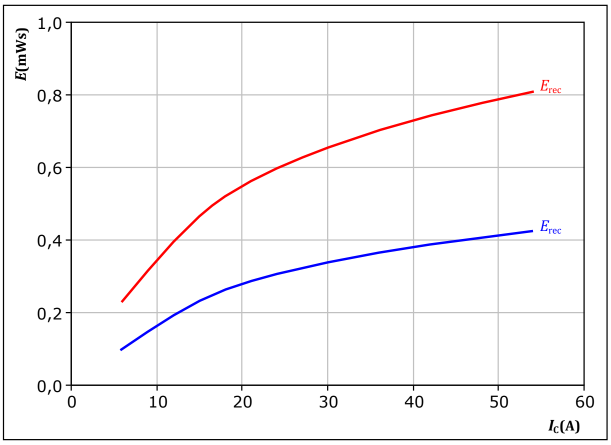
With an inductive load at

V_{CE} =	350	V	T_j: 25 °C / 125 °C
V_{GE} =	±15	V	
I_C =	30	A	

figure 35. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_C)$



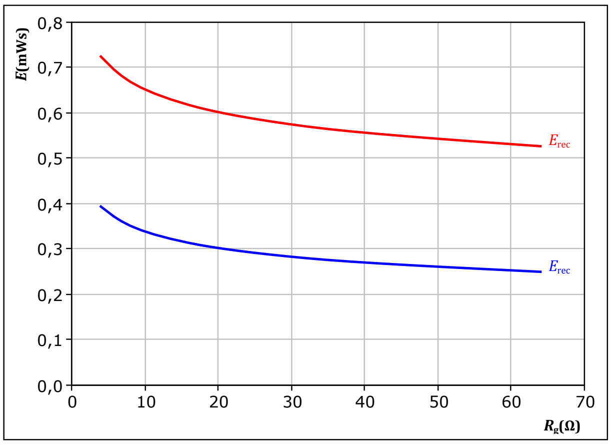
With an inductive load at

V_{CE} =	350	V	T_j: 25 °C / 125 °C
V_{GE} =	±15	V	
R_{gon} =	16	Ω	

figure 36. **FWD**

Typical reverse recovered energy loss as a function of IGBT turn on gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

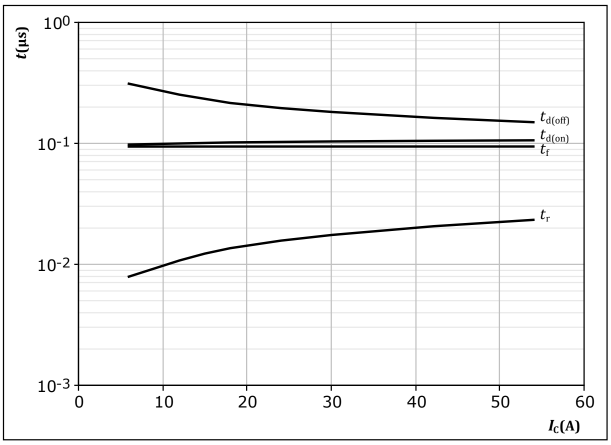
V_{CE} =	350	V	T_j: 25 °C / 125 °C
V_{GE} =	±15	V	
I_C =	30	A	

Boost Switching Characteristics

figure 37. **IGBT**

Typical switching times as a function of collector current

t = f(I_C)



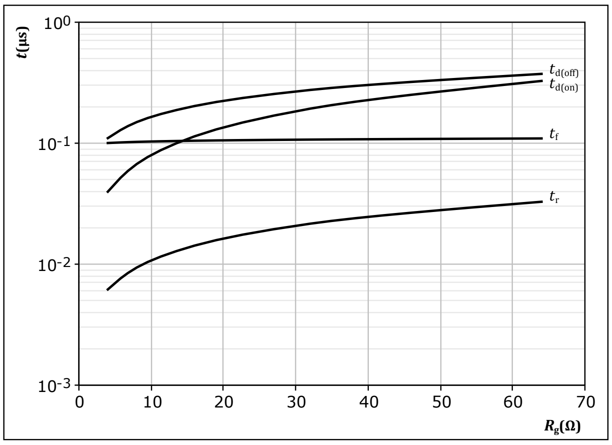
With an inductive load at

T_j =	125	°C
V_{CE} =	350	V
V_{GE} =	±15	V
R_{gon} =	16	Ω
R_{goff} =	16	Ω

figure 38. **IGBT**

Typical switching times as a function of IGBT turn on gate resistor

t = f(R_g)



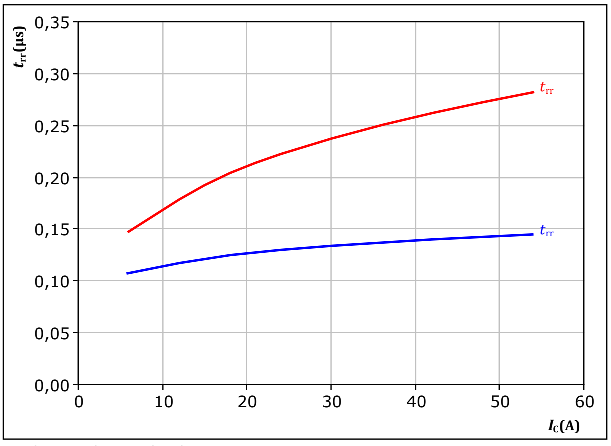
With an inductive load at

T_j =	125	°C
V_{CE} =	350	V
V_{GE} =	±15	V
I_C =	30	A

figure 39. **FWD**

Typical reverse recovery time as a function of collector current

t_{rr} = f(I_C)



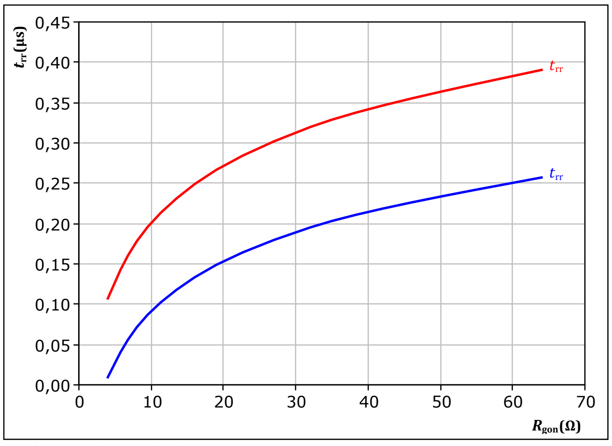
With an inductive load at

V_{CE} =	350	V
V_{GE} =	±15	V
R_{gon} =	16	Ω

figure 40. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

t_{rr} = f(R_{gon})



With an inductive load at

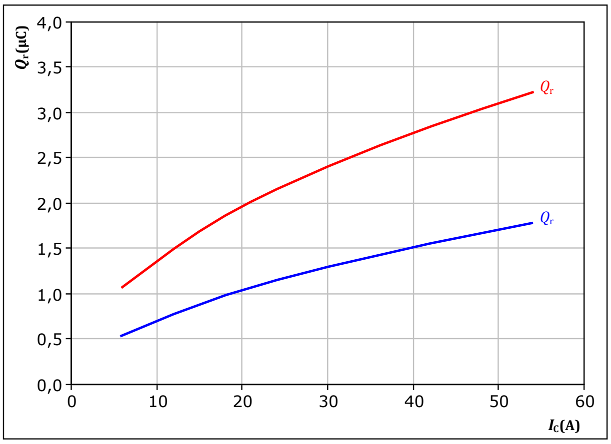
V_{CE} =	350	V
V_{GE} =	±15	V
I_C =	30	A

Boost Switching Characteristics

figure 41. **FWD**

Typical recovered charge as a function of collector current

Q_r = f(I_C)



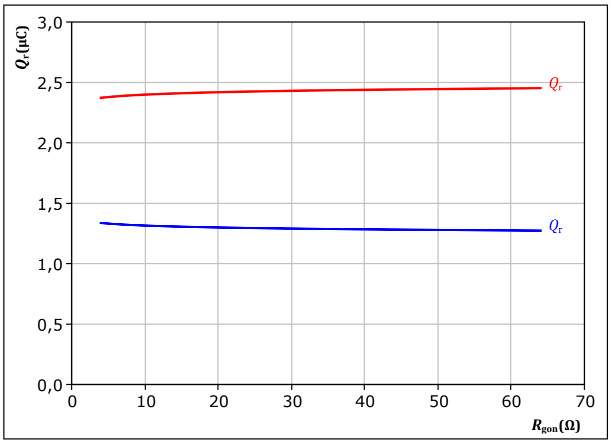
With an inductive load at

V_{CE} =	350	V	T_j: 25 °C (blue), 125 °C (red)
V_{GE} =	±15	V	
R_{gon} =	16	Ω	

figure 42. **FWD**

Typical recovered charge as a function of IGBT turn on gate resistor

Q_r = f(R_{gon})



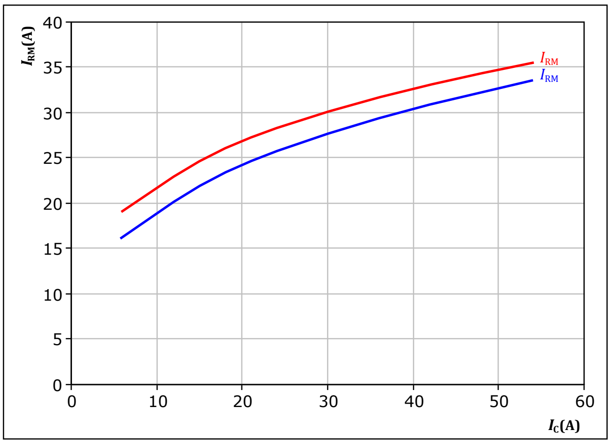
With an inductive load at

V_{CE} =	350	V	T_j: 25 °C (blue), 125 °C (red)
V_{GE} =	±15	V	
I_C =	30	A	

figure 43. **FWD**

Typical peak reverse recovery current as a function of collector current

I_{RM} = f(I_C)



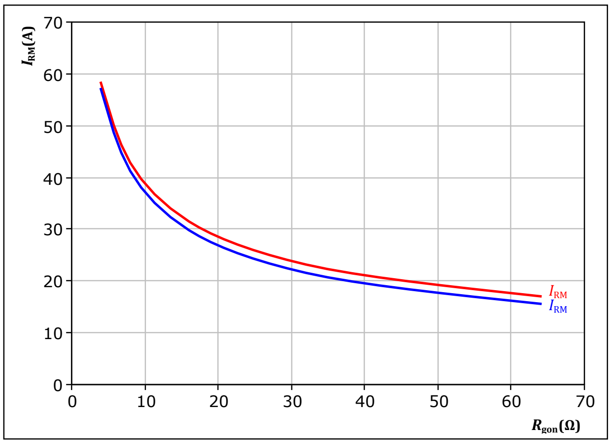
With an inductive load at

V_{CE} =	350	V	T_j: 25 °C (blue), 125 °C (red)
V_{GE} =	±15	V	
R_{gon} =	16	Ω	

figure 44. **FWD**

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

I_{RM} = f(R_{gon})



With an inductive load at

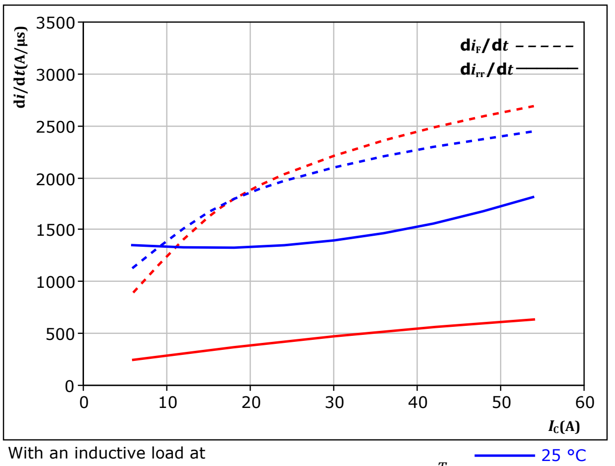
V_{CE} =	350	V	T_j: 25 °C (blue), 125 °C (red)
V_{GE} =	±15	V	
I_C =	30	A	

Boost Switching Characteristics

figure 45. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, di_{rr}/dt = f(I_C)



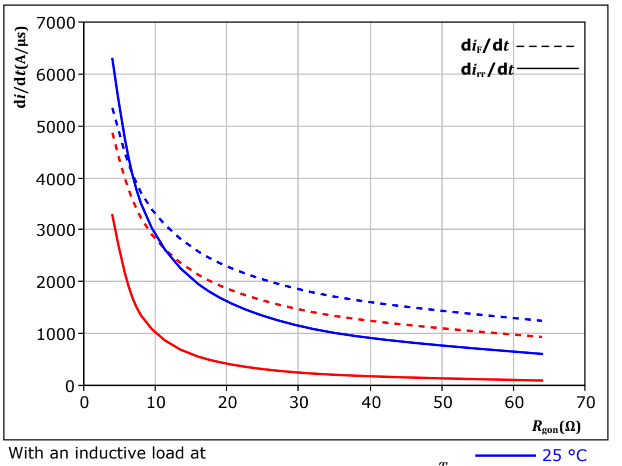
With an inductive load at

V_{CE} =	350	V	T_j: 25 °C
V_{GE} =	±15	V	125 °C
R_{gon} =	16	Ω	

figure 46. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})



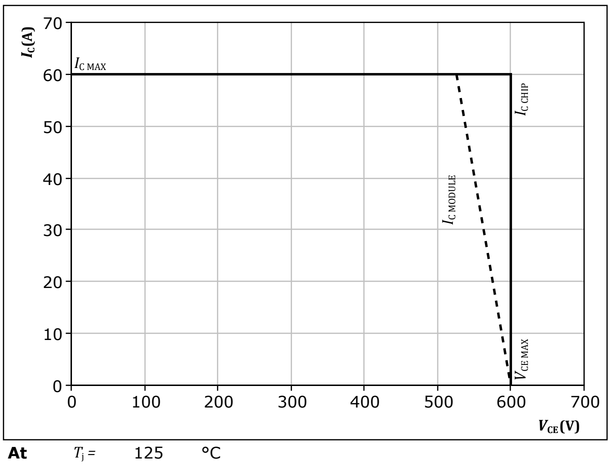
With an inductive load at

V_{CE} =	350	V	T_j: 25 °C
V_{GE} =	±15	V	125 °C
I_C =	30	A	

figure 47. **IGBT**

Reverse bias safe operating area

I_C = f(V_{CE})



At	T_j =	125	°C
	R_{gon} =	16	Ω
	R_{goff} =	16	Ω

Switching Definitions

figure 48. **IGBT**

Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{tEoff} **= integrating time for** E_{off})

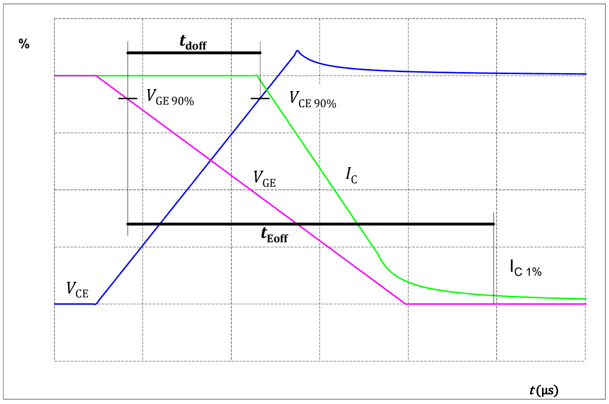


figure 49. **IGBT**

Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} **= integrating time for** E_{on})

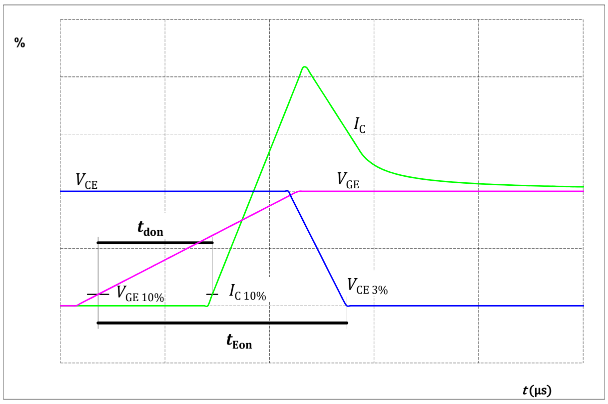


figure 50. **IGBT**

Turn-off Switching Waveforms & definition of t_f

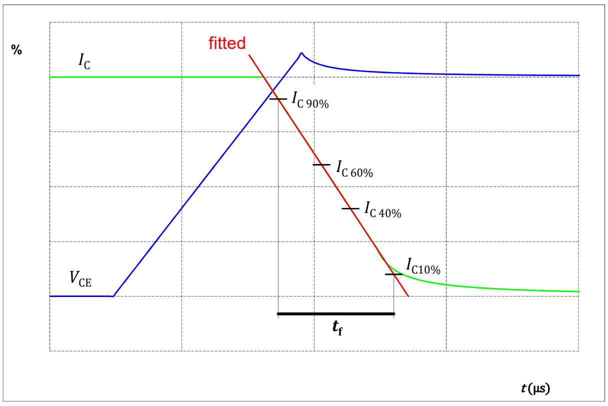
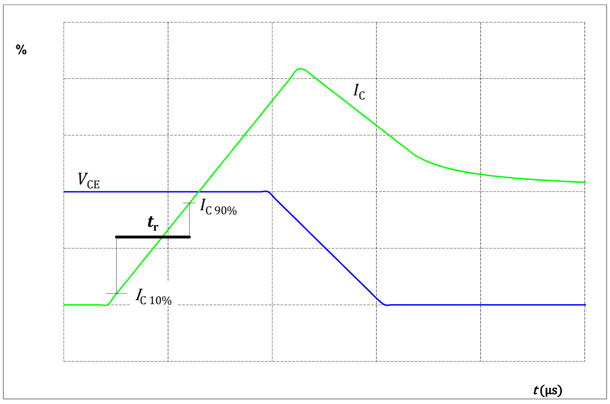


figure 51. **IGBT**

Turn-on Switching Waveforms & definition of t_r



Switching Definitions

figure 52. **FWD**

Turn-off Switching Waveforms & definition of t_{rr}

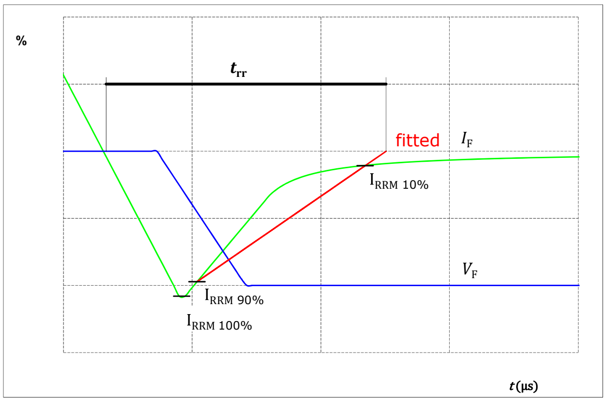
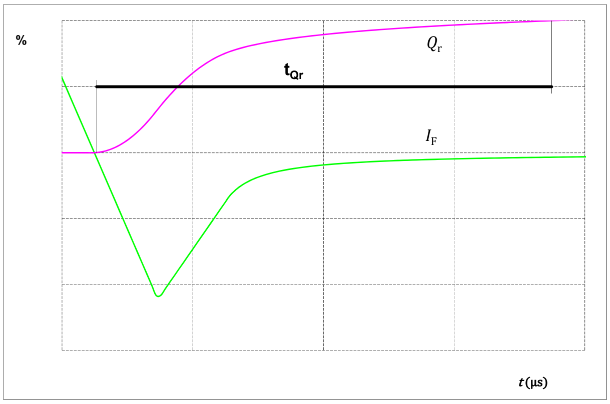


figure 53. **FWD**

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



Vincotech

Ordering Code

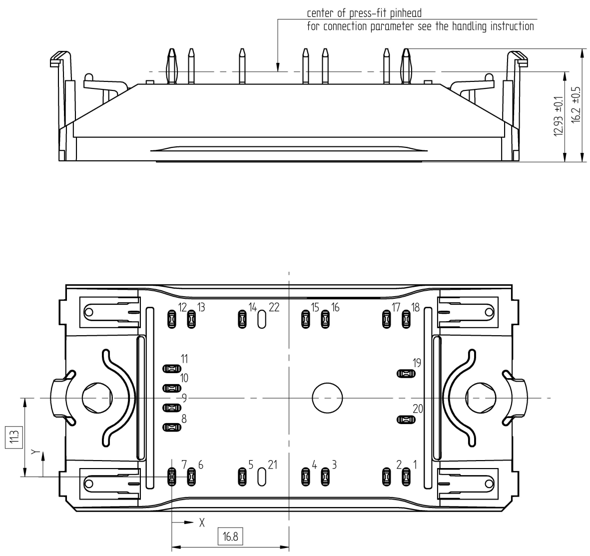
Version	Ordering Code
Without thermal paste	10-PZ06NIA030SA-P924F33Y
With thermal paste (5,2 W/mK, PTM6000HV)	10-PZ06NIA030SA-P924F33Y-/7/
With thermal paste (3,4 W/mK, PSX-P7)	10-PZ06NIA030SA-P924F33Y-/3/

Marking

	Name		Date code	UL & VIN	Lot	Serial
Text	NN-NNNNNNNNNNNNNN-TTTTTTVV		WWYY	UL VIN	LLLLL	SSSS
Datamatrix	Type&Ver	Lot number	Serial	Date code		
	TTTTTTTVV	LLLLL	SSSS	WWYY		

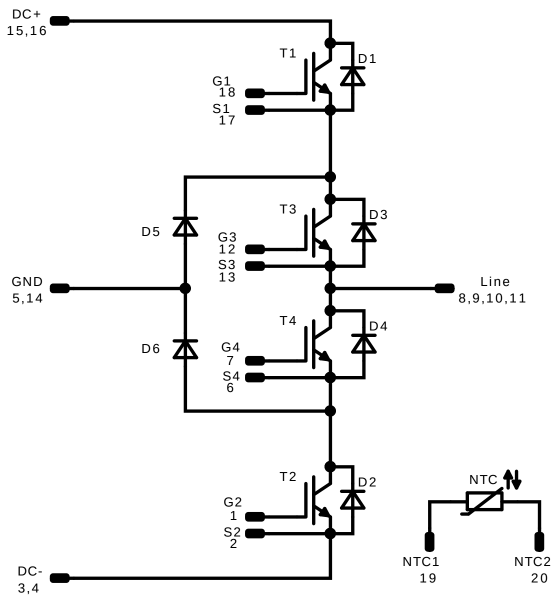
Outline

Pin table [mm]			
Pin	X	Y	Function
1	33,6	0	G2
2	30,8	0	S2
3	22	0	-DC
4	19,2	0	-DC
5	10,1	0	GND
6	2,8	0	S4
7	0	0	G4
8	0	7,1	Line
9	0	9,9	Line
10	0	12,7	Line
11	0	15,5	Line
12	0	22,6	G3
13	2,8	22,6	S3
14	10,1	22,6	GND
15	19,2	22,6	+DC
16	22	22,6	+DC
17	30,8	22,6	S1
18	33,6	22,6	G1
19	33,6	14,8	NTC1
20	33,6	8,2	NTC2
21	not assembled		
22	not assembled		



Tolerance of pinpositions: ±0,5mm at the end of pins
Dimension of coordinate axis is only offset without tolerance

Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T1, T2	IGBT	600 V	30 A	Buck Switch	
D5, D6	FWD	600 V	30 A	Buck Diode	
T3, T4	IGBT	600 V	30 A	Boost Switch	
D2, D1	FWD	600 V	30 A	Boost Diode	
D4, D3	FWD	600 V	30 A	Boost Sw. Inv. Diode	
NTC	Thermistor			Thermistor	

Packaging instruction				
Standard packaging quantity (SPQ) 135	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* 0 packages see vincotech.com website.

Package data
Package data for *flow* 0 packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
10-PZ06NIA030SA-P924F33Y-D1-14	4 May. 2022		